

Product data sheet

1. General description

Dual ultrafast power diode in a TO263 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- Soft recovery characteristic minimizes power consuming oscillations
- Surface-mountable package

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Symbol	Parameter	Conditions		Values			Unit
-	maximum rating	1					
V_{RRM}	repetitive peak reverse voltage			20	00		V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u>		2	0		A
I _{RRM}	repetitive peak reverse current	δ = 0.001; t _p = 2 μs;	0.2		A		
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	8		kV		
Static ch	aracteristics	· · · · · ·					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-		0.72	0.85	V
		I _F = 20 A; T _j = 25 °C	-		1	1.15	V
Dynamic	characteristics	· ·	I	(
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5$	-		20	25	ns

5. Pinning information

Table 2.	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode [1]		
3	A2	anode 2		
mb	К	mounting base; cathode	1 0-263 (D2PAK)	K sym125

[1] it is not possible to make a connection to pin 2 of the TO263 package

6. Ordering information

Table 3. Ordering information

Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	Name		method	quantity	version	issue date
BYV32EB-200	TO263	BYV32EB-200,118	Reel	800	TO263N	26-Sep-2016

7. Marking

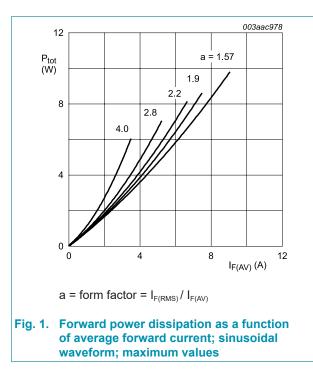
Table 4. Marking codes					
	Type number	Marking codes			
	BYV32EB-200	BYV32EB-200			

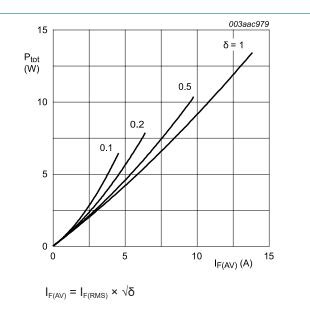
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V _R	reverse voltage	DC	200	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u>	20	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; per diode	20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	A
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	A
I _{RRM}	repetitive peak reverse current	δ = 0.001; t _p = 2 µs; per diode	0.2	A
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs; per diode	0.2	A
T _{stg}	storage temperature		-40 to 150	°C
Tj	junction temperature		150	°C
V_{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k Ω	8	kV

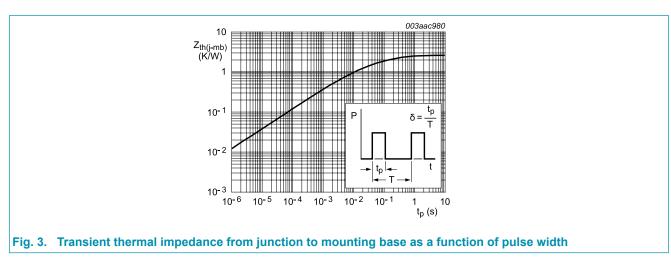






9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient		-	60	-	K/W



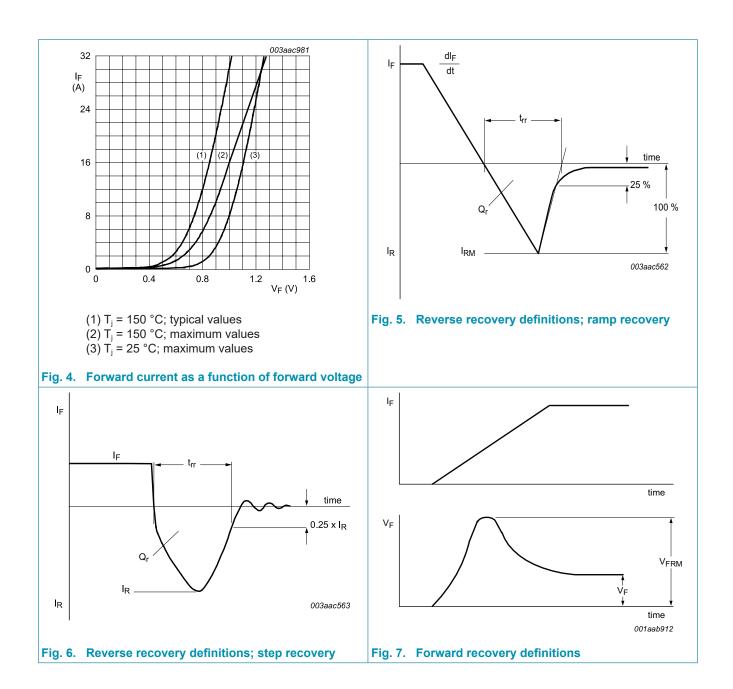
Dual ultrafast power diode

10. Characteristics

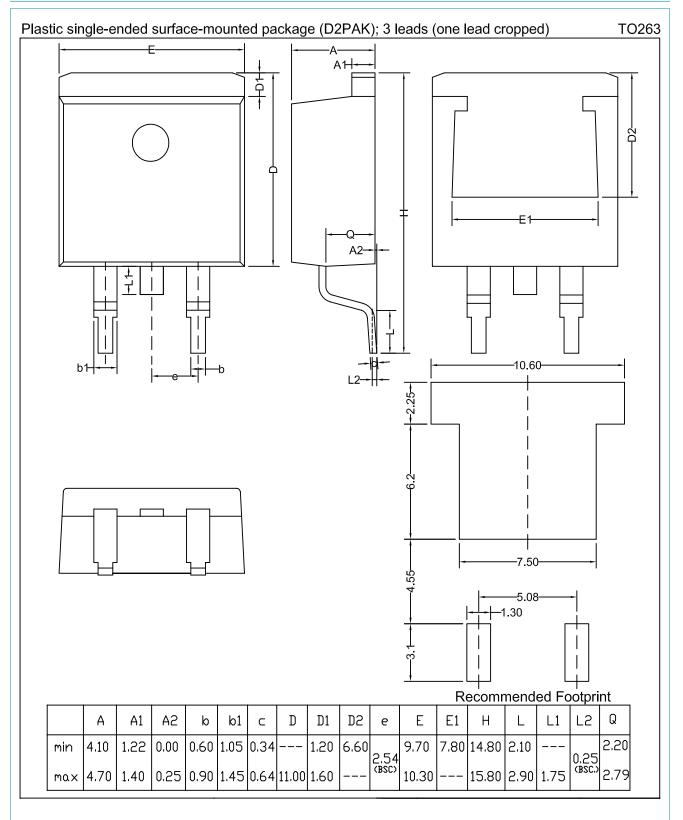
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
	racteristics						
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V
		I _F = 20 A; T _j = 25 °C		-	1	1.15	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C		-	6	30	μA
		V _R = 200 V; T _j = 100 °C		-	0.2	0.6	mA
Dynamic	characteristics		· · ·				
Qr	recovered charge	I_{F} = 2 A; V_{R} = 30 V; dI_{\text{F}}/dt = 20 A/µs; T_{j} = 25 °C		-	8	12.5	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; ramp recovery; <u>Fig. 5</u>		-	20	25	ns
		$I_{\text{F}} = 0.5 \text{ A to } I_{\text{R}} = 1 \text{ A}; T_{\text{j}} = 25 \text{ °C};$ measured at $I_{\text{R}} = 0.25 \text{ A};$ step recovery; <u>Fig. 6</u>		-	10	20	ns
V _{FR}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 7</u>		-	-	1	V

Dual ultrafast power diode

BYV32EB-200



11. Package outline



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Dual ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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	Features and benefits

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